

Insulating Phases

Old-fashioned equilibrium systems
extrapolated from non-zero T to $T=0$

S.A. Kivelson

Localization at the Edge of 2D Topological Insulator by Kondo Impurities

Boris Altshuler, Stanford, Nov. 5, 2015

Kondo spins coupled to a chiral Luttinger Liquid

Altshuler, Aleiner, Yudson, Phys. Rev. Lett. **111**, 86401 (2013)

Yevtushenko, Wugalter, Yudson, Altshuler, arXiv:1505.04820

Are topologically protected edge states really
topologically protected in “real” solids?

Many-body localization is certainly profound and new

Is it relevant to the properties of “real” materials?

Or is it always destroyed by phonon-induced VRH?

And even if so, are there phenomena for which such effects are weak enough that it is useful to think of “almost” MBL?

“I would like to mention that insulators,
i.e. conductors with resistance much larger than h/e^2
in which the resistance increases as the temperature decreases,
have never been studied in detail.”

Best,
Boris

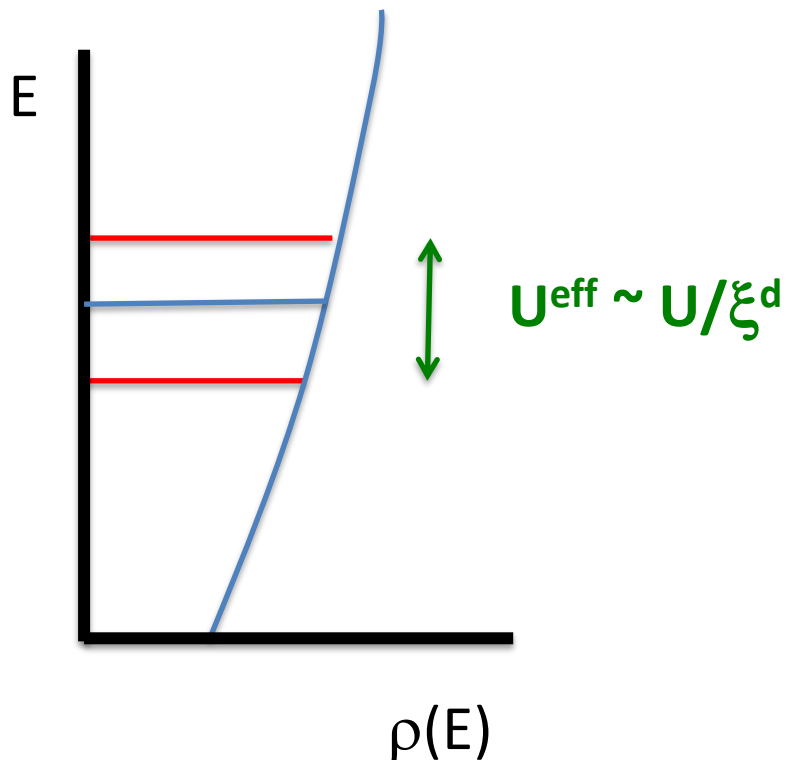
Boris Spivak that is

Moreover, when I asked him, Elihu Abrahams concurred

Why there is (probably) no such thing
as an interacting Anderson insulator

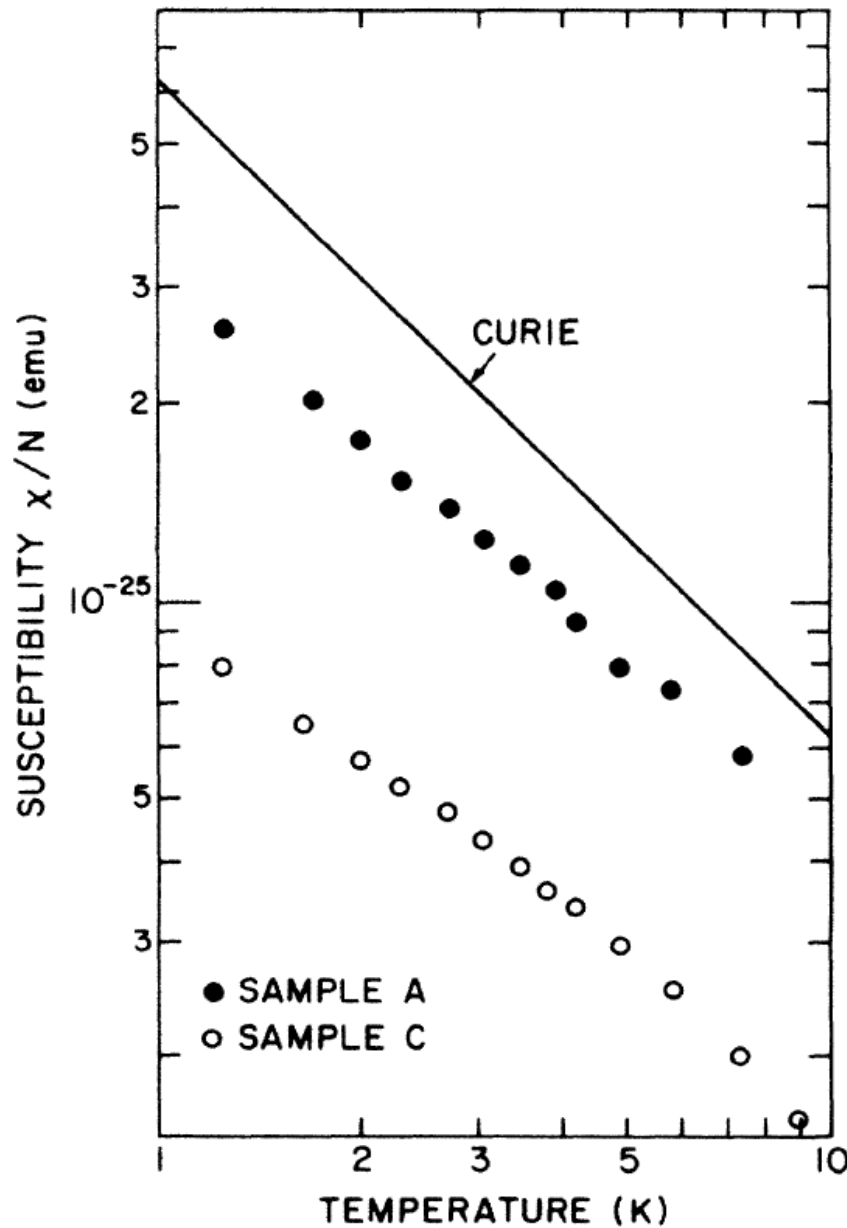
Why there is (probably) no such thing as an interacting Anderson insulator

Effect of weak repulsive interactions:



$$n_{\text{spin}} \sim \rho(E_F) U^{\text{eff}}$$

Probably leads to spin-glass
or random singlet phase.



Here is the magnetic susceptibility of strongly insulating P doped Si

A) $n_p = 6.7 \times 10^{17} \text{ cm}^{-3}$

B) $n_p = 2.4 \times 10^{18} \text{ cm}^{-3}$

M.P. Sarachik *et al*

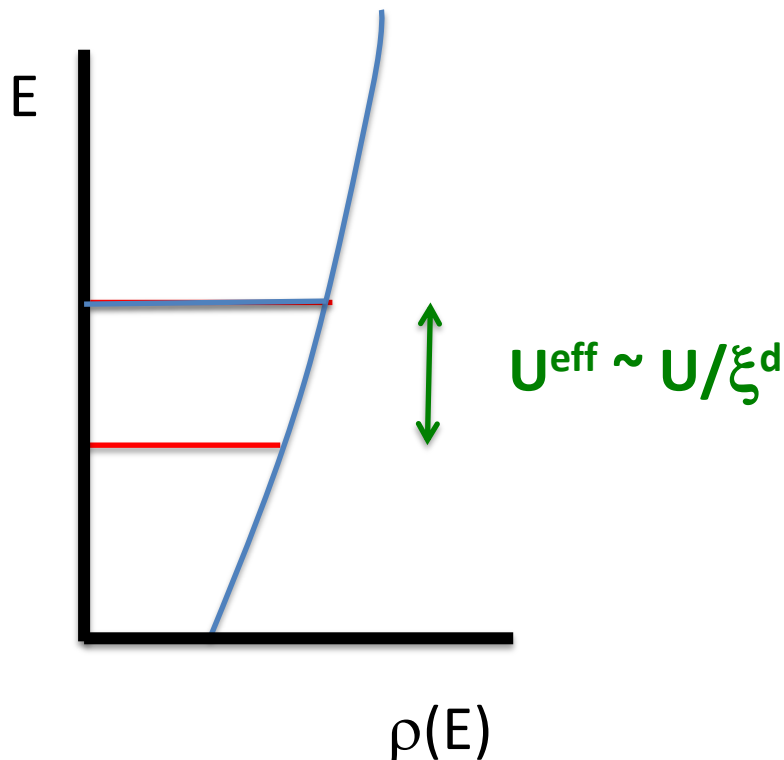
Phys. Rev. B **34**, 387 (1986).

(positive sign corresponds to paramagnetism)

(An Anderson insulator would exhibit Pauli paramagnetism)

Why there is (probably) no such thing as an interacting Anderson insulator

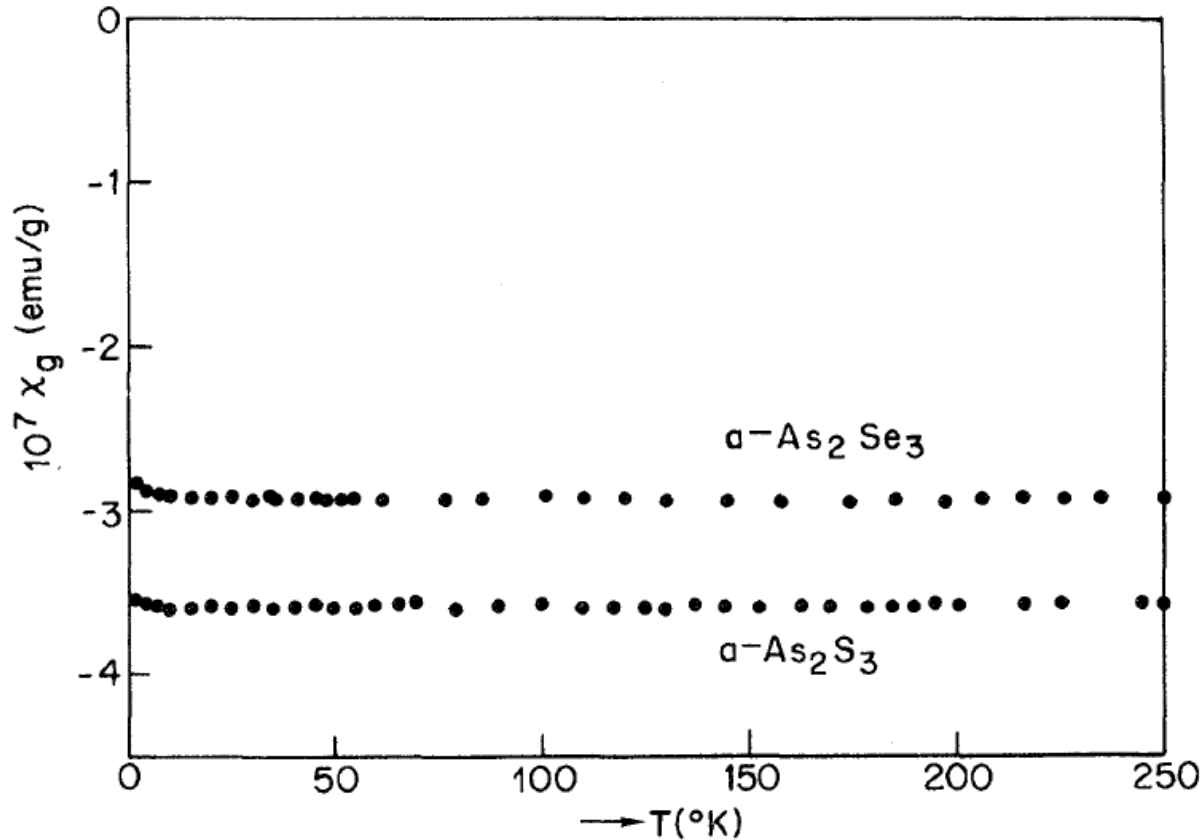
Effect of weak attractive interactions:



$$\Delta_{\text{spin}} \sim \rho(E_F) U^{\text{eff}}$$

“Anderson negative U centers”
spin-gap, but no charge gap

Magnetic susceptibility of amorphous chalcogenide glasses



Strongly insulating
(conductivity is
“activated”)

Large optical gap

Diamagnetic

Pinning of Fermi
energy indicates
large density of
states at Fermi
energy
(compressible)

Bosonic insulator – pairing without SC

Conjecture: For electrons with spin, effects of interactions in an Anderson insulator are never perturbative

Spin-orbit coupling probably does not affect this conclusion so long as Kramers degeneracy maintained

However, the presence of a Zeeman field may be a game changer.

Equilibration in a disordered insulator

Phonons and variable range hopping.

Variable-range-hopping (VRH) in neutron-transmuted doped GaAs

Rentzsch *et al*, Physica Status Solidi
B **137**, 691 (1986).

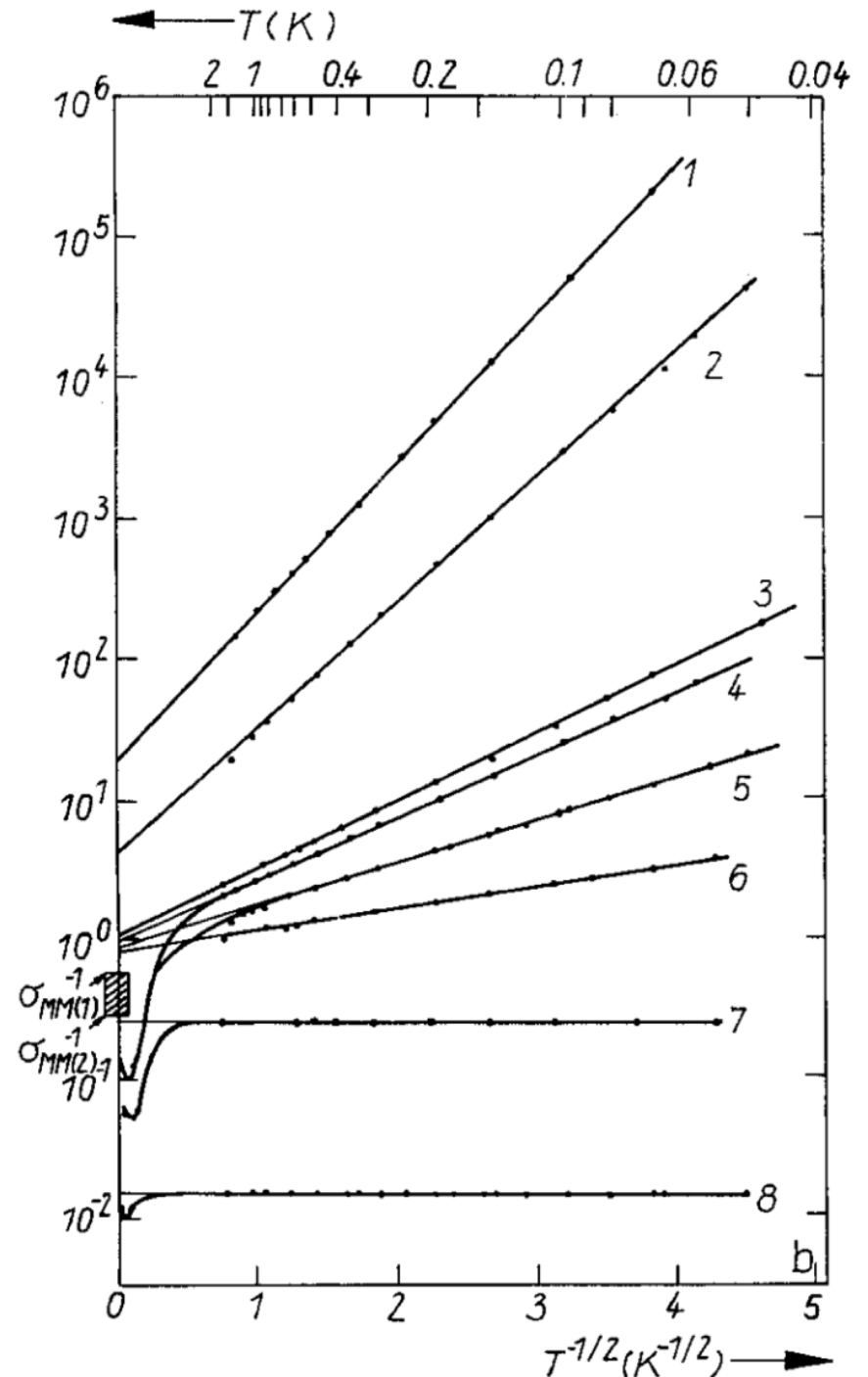
(y axis in Ohm-cm)

$$\rho(T) = \rho_0 \exp[(T_0/T)^\alpha]$$

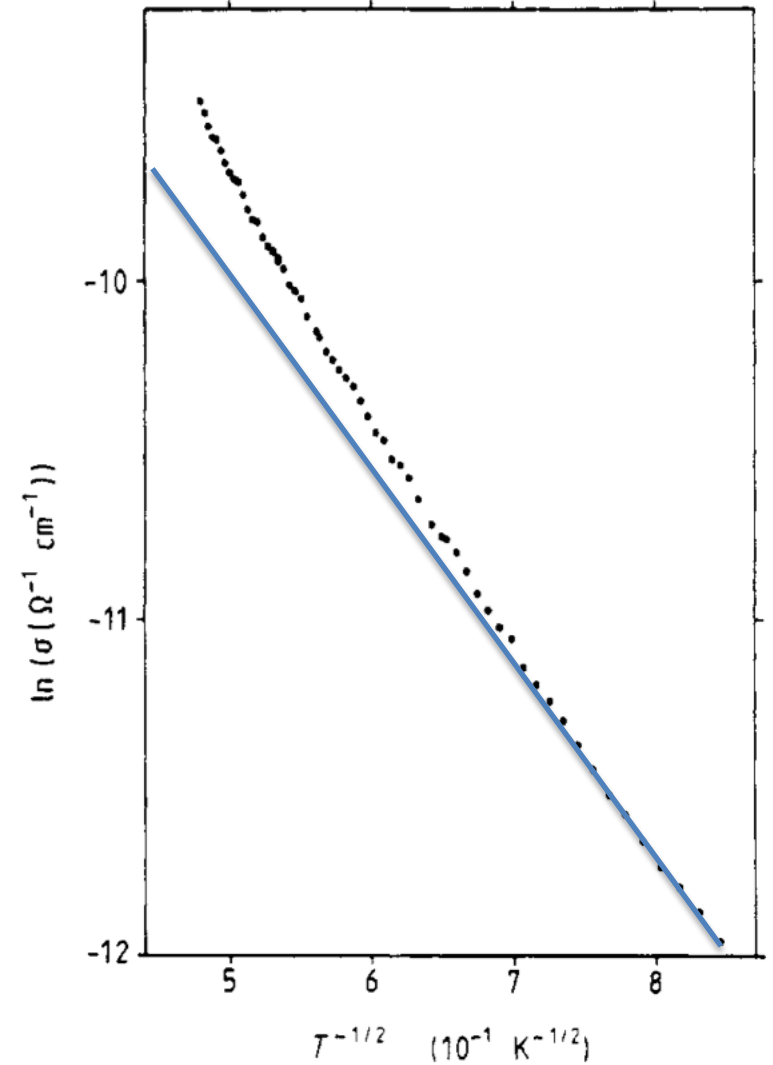
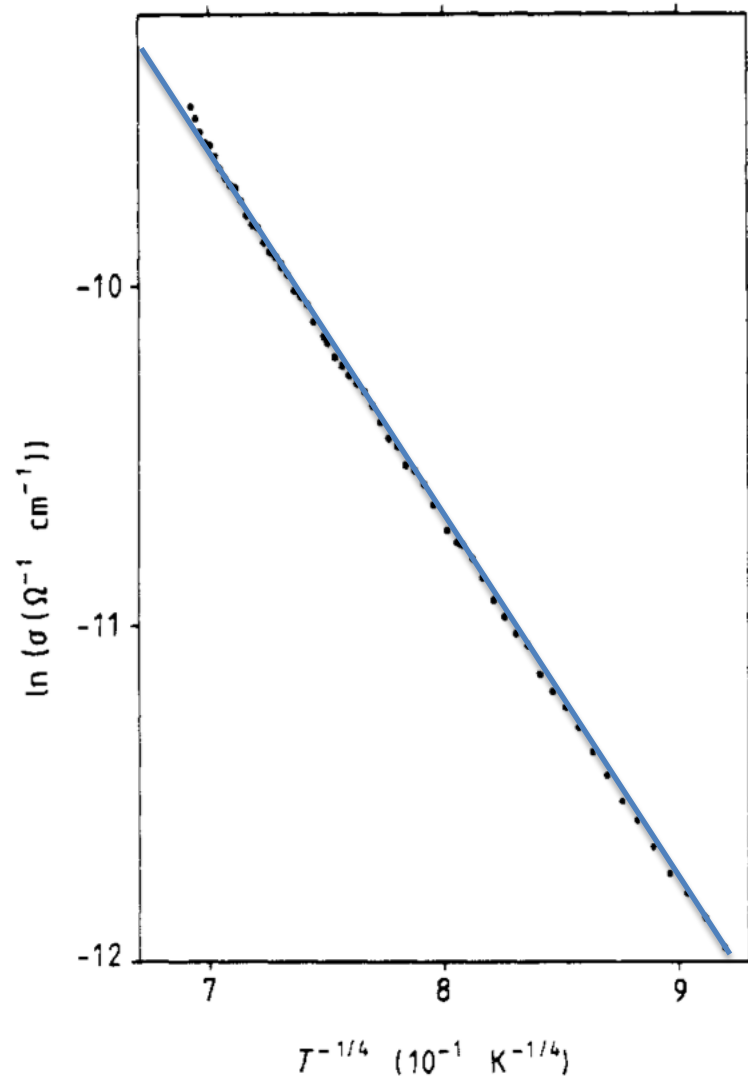
$\alpha = 1$ “activated”

$\alpha = 1/(d + 1)$ Mott VRH

$\alpha = 1/2$ Efros – Shklovski VRH

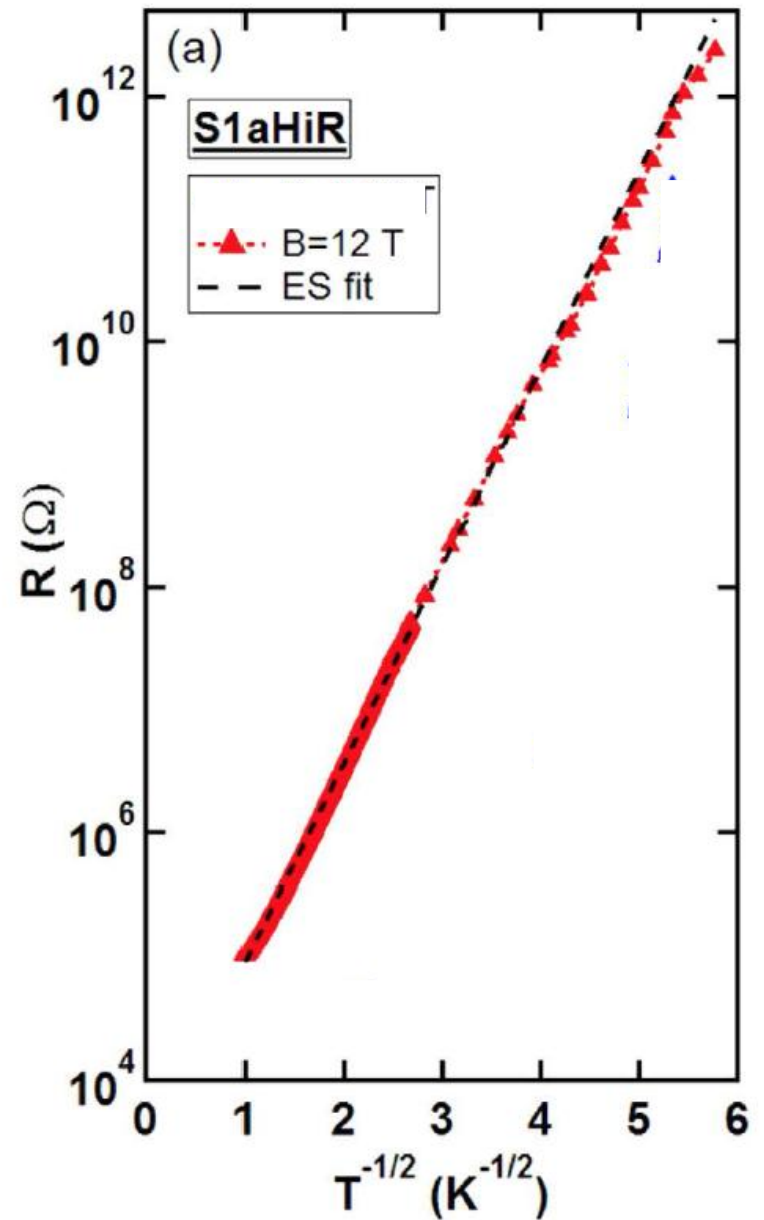


Compensated n-InP – M. Benzaguen *et al*, Journal of Phys. C: Solid State Phys. **18**, L1008 (1985)



InO Film for $B > B_{\text{SIT}} \sim 0.5 \text{ T}$

M. Ovadia *et al*,
Scientific Reports **5**, 13503
(2015)



The “Hall insulator” in 2D, and its relation to the QHIT and the SIT

$$\sigma_{xx}(T) \rightarrow 0 \quad \text{and} \quad \sigma_{xy} \rightarrow 0 \quad \text{as} \quad T \rightarrow 0$$

$$\rho_{xx}(T) \rightarrow \infty \quad \text{and} \quad \rho_{xy} \sim B/nec \quad \text{as} \quad T \rightarrow 0$$

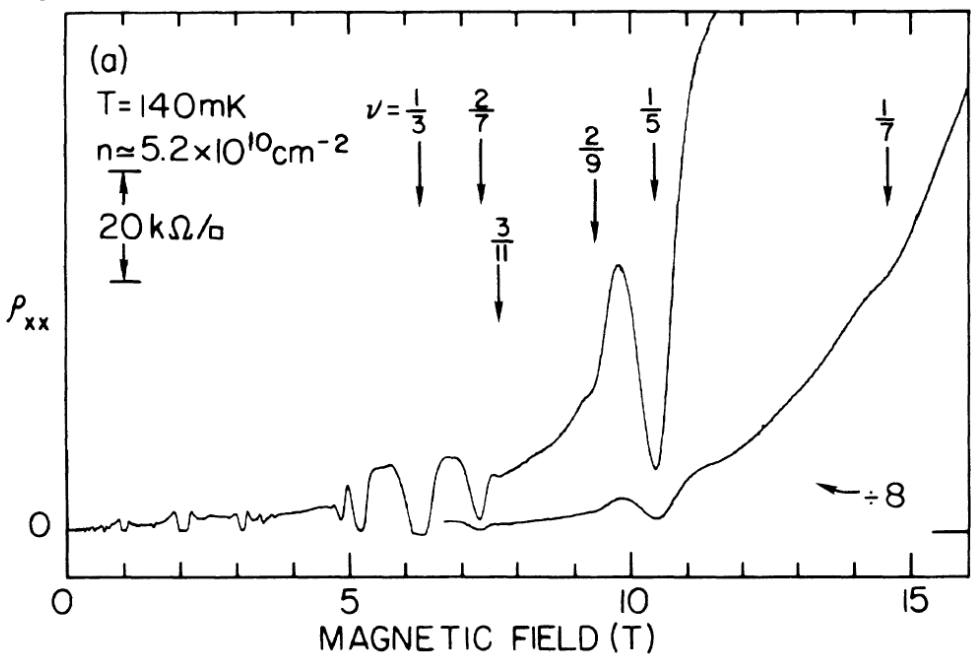
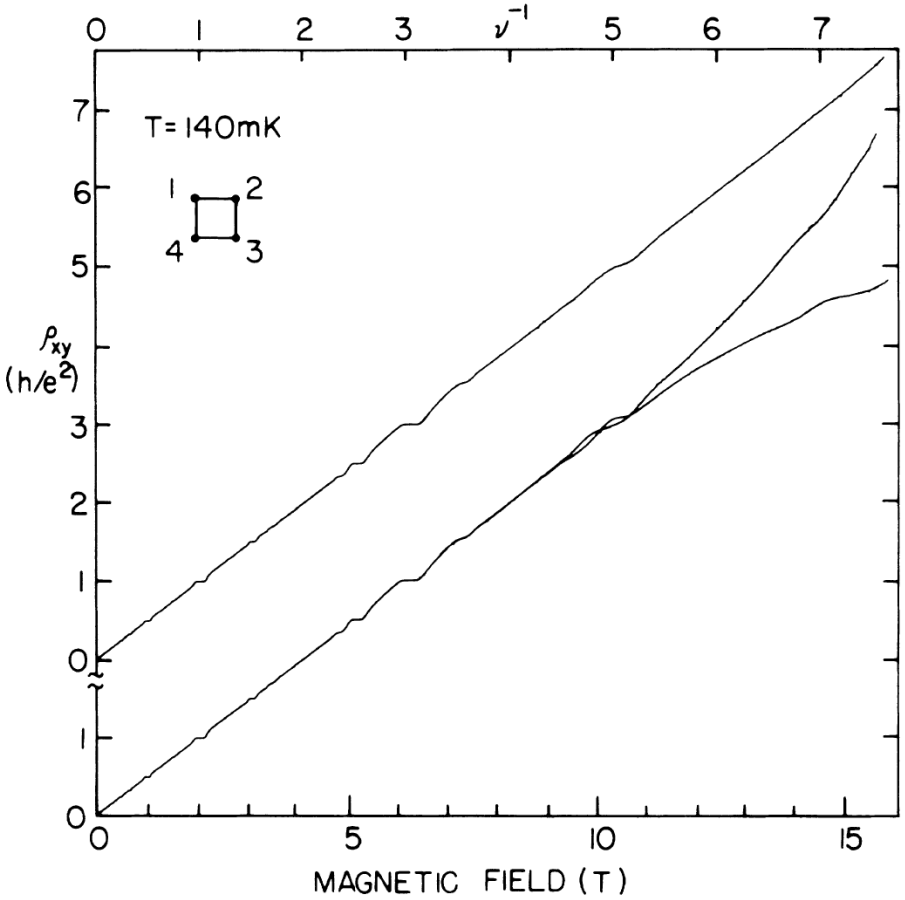
$$\rho_{xy} = \frac{-\sigma_{xy}}{[\sigma_{xx}]^2 + [\sigma_{xy}]^2} \rightarrow \text{const} \quad \text{if} \quad \sigma_{xy} \sim [\sigma_{xx}]^2$$

SAK, D.H. Lee, and S-C. Zhang, PRB **46**, 2223 (1992).

O.Entin-Wohman, A.G. Aronov, Y. Levinson, and Y. Imry, PRL **75**, 4094 (1995)
(Addressed in the context of VRH and the Holstein model)

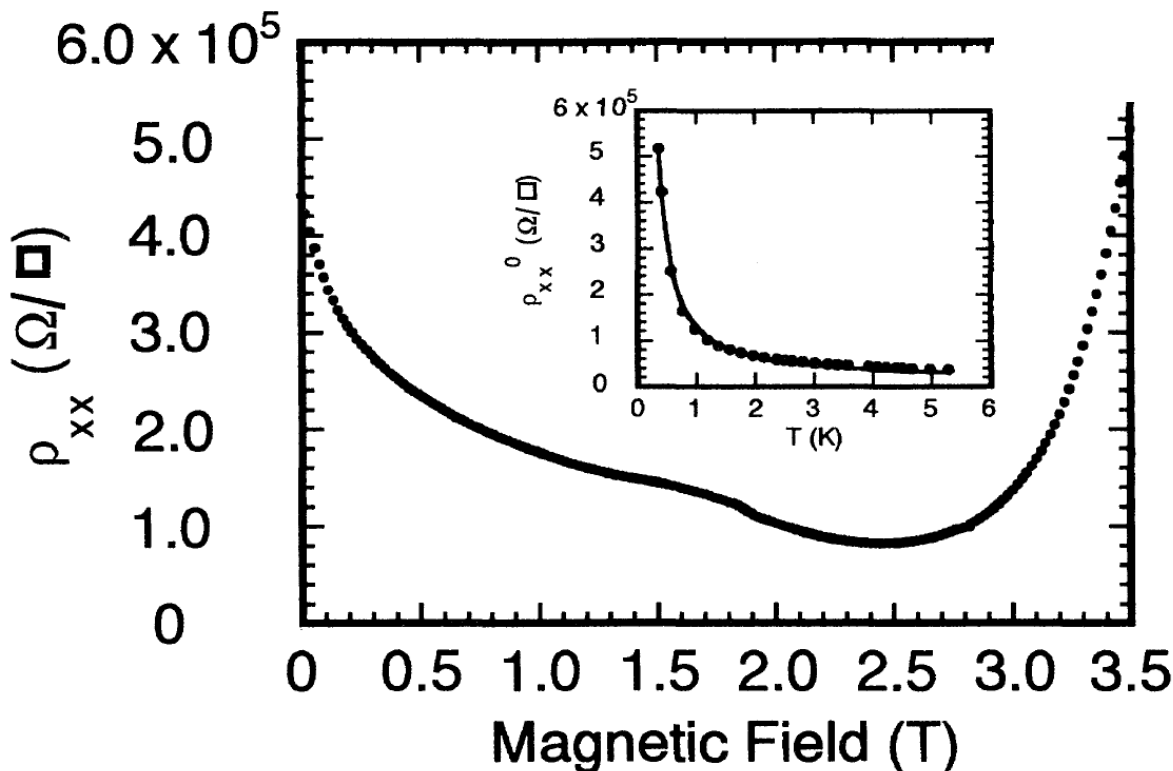
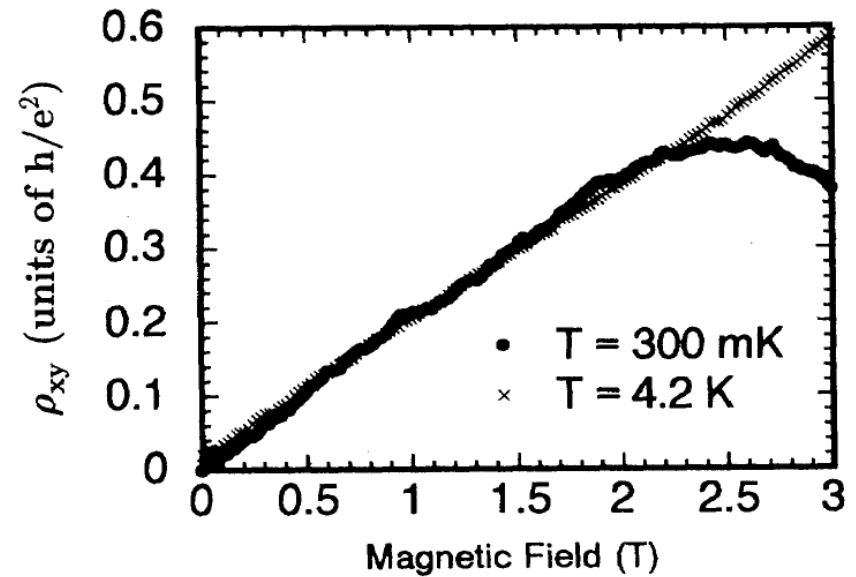
High mobility GaAs/AlGaAs heterostructure

Goldman, Shayegan, Tsui
 Phys. Rev. Lett. **61**,881 (1988)



Von Klitzing constant
 $R_K = h/e^2$
 $= 25.12807557 \text{ k}\Omega$

Low Mobility GaAs/AlGaAs
heterostructure
Johnson and Jiang,
Phys. Rev. B**48**, 2823 (1993)

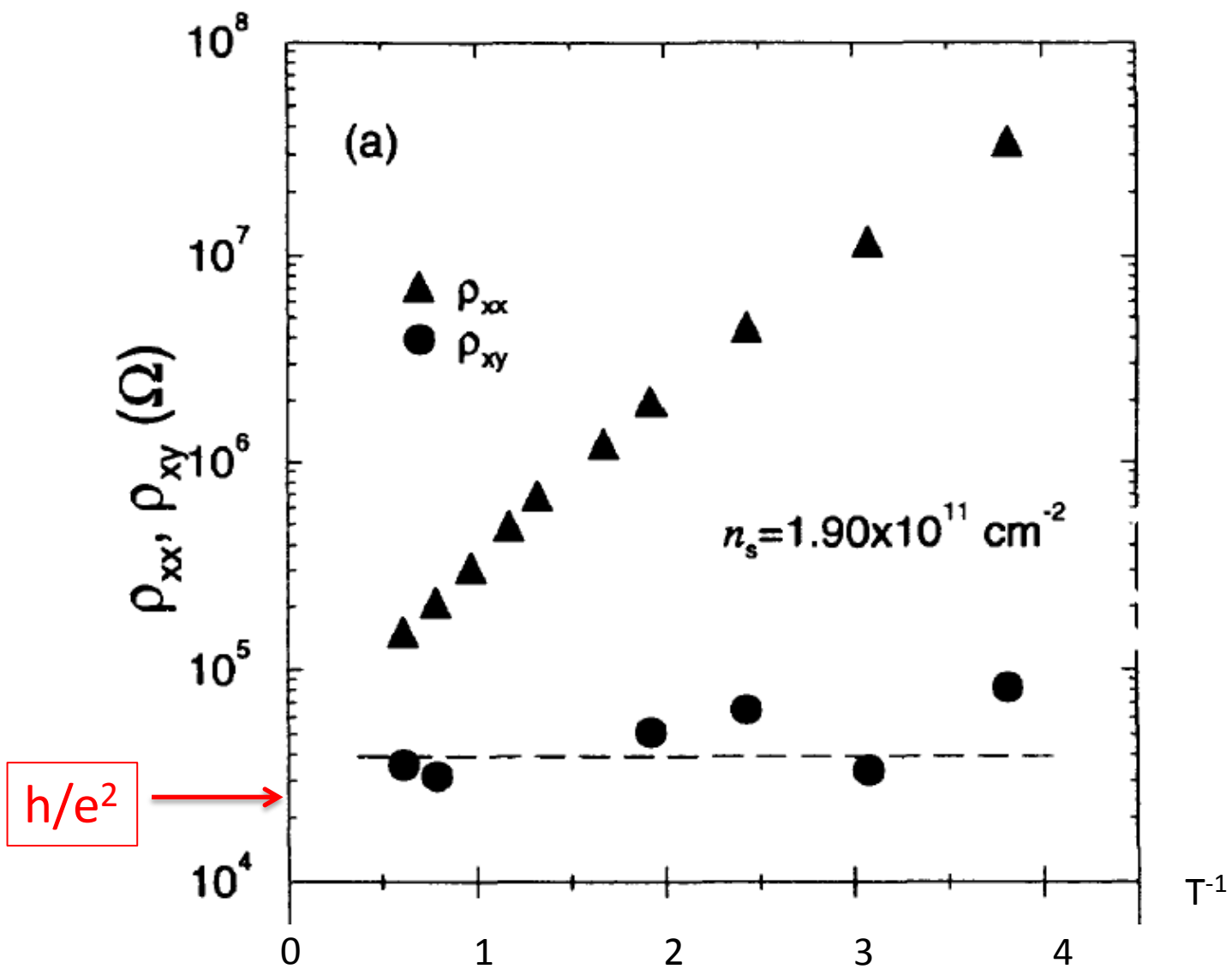


S
i

M
O
S
F
E
T

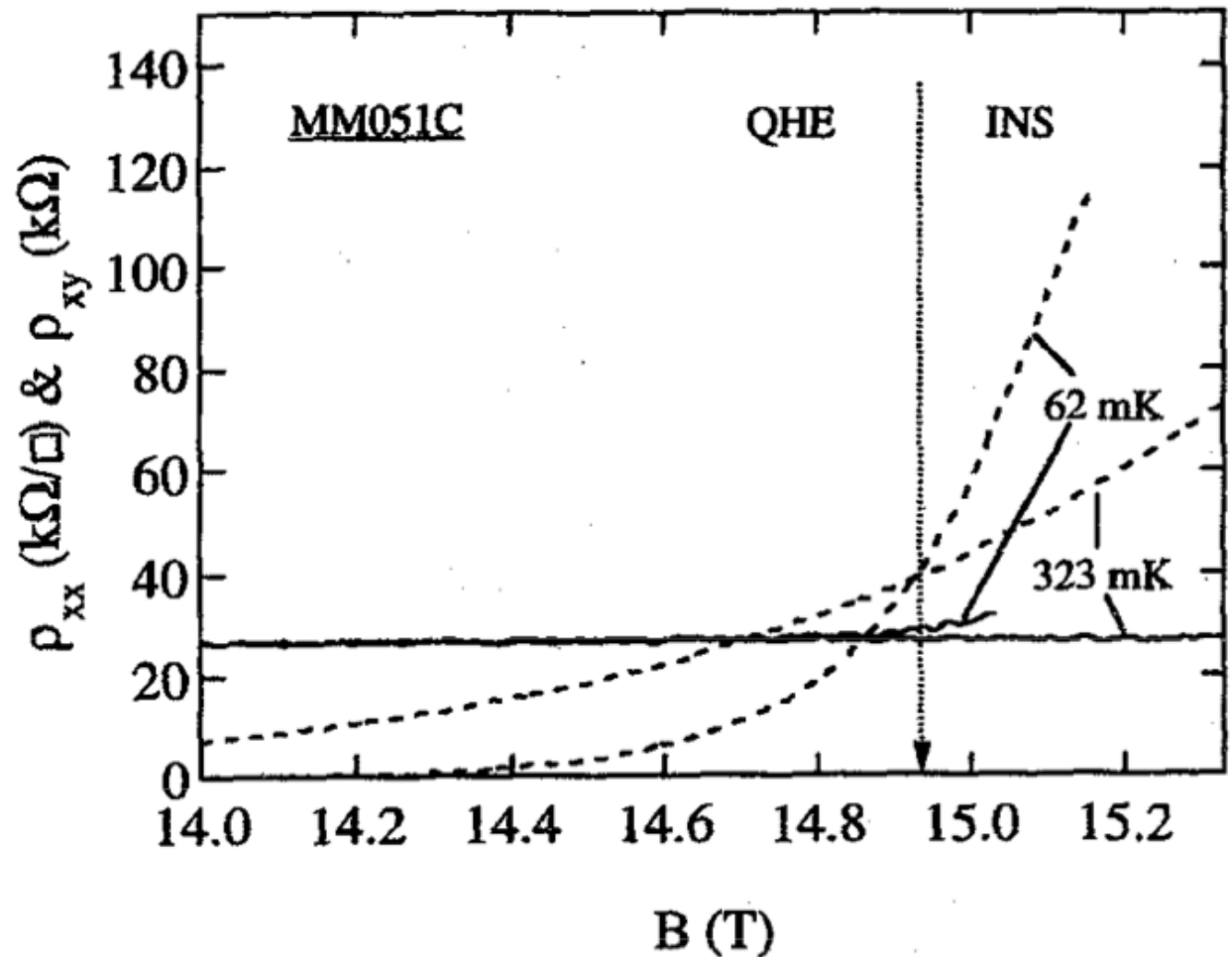
w
i
t
h

n
=



Hall insulator proximate to the QHIT

Shahar, Tsui, Shayegan, Cunningham,
Shimshoni, and Sondhi, Solid State
Commun. **102**, 817 (1997).

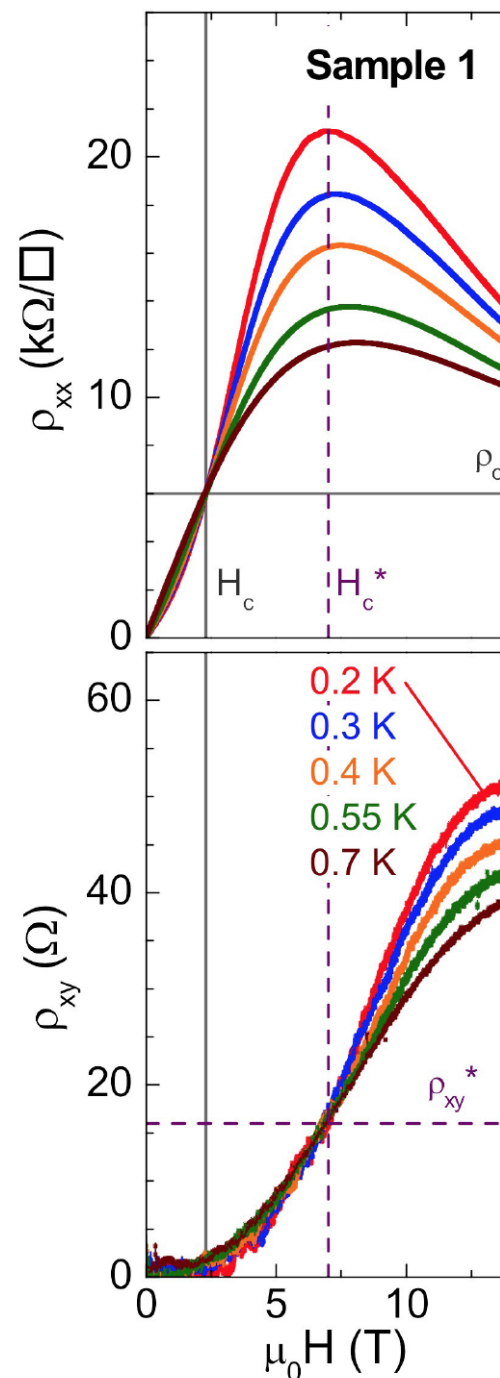
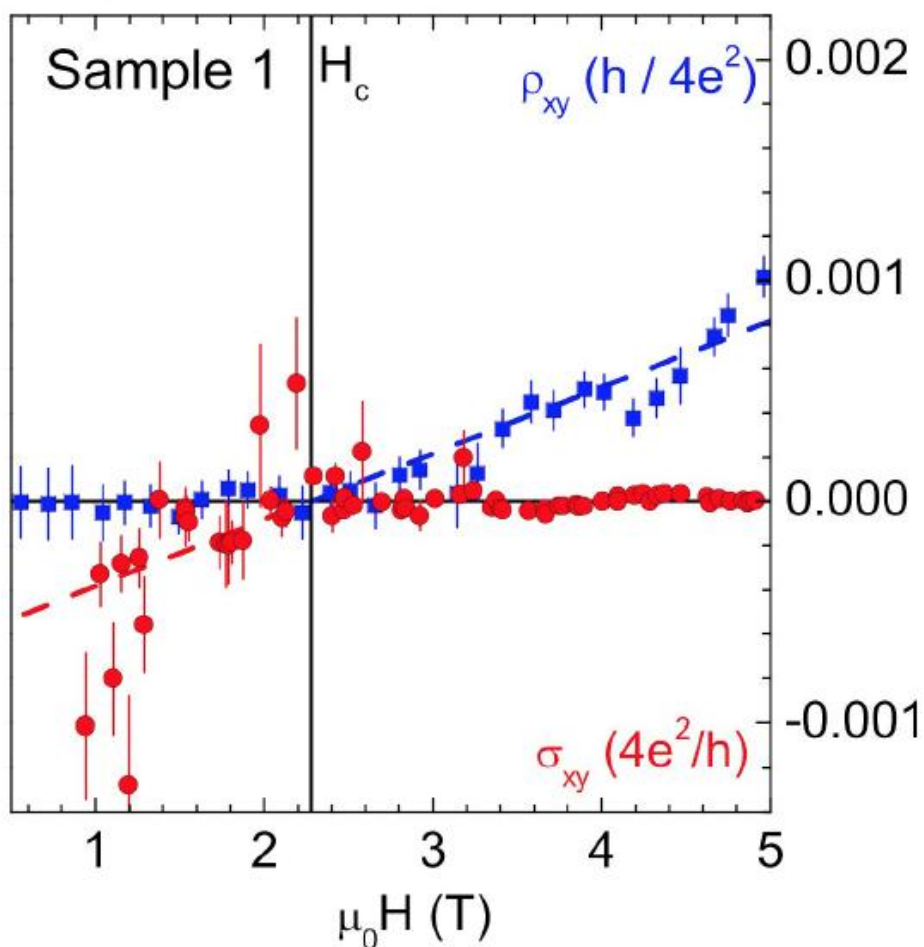


Hall Insulator close to the SIT in InO films

with $B_{\text{SIT}} \sim 3\text{T}$

Breznay, Steiner, SAK, Kapitulnik

arXiv 2015



Equilibration in a disordered insulator

Phonons and variable range hopping.

But is there any evidence of a finite T “almost” transition to an insulating state?

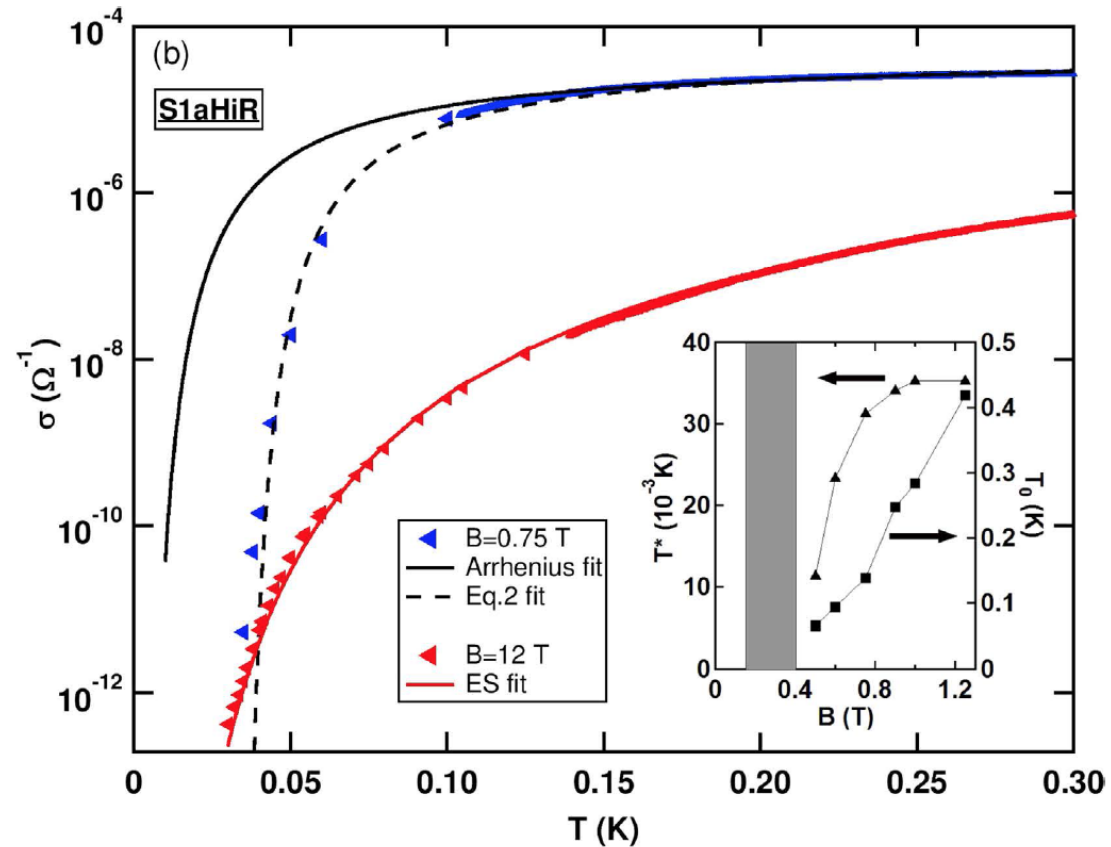
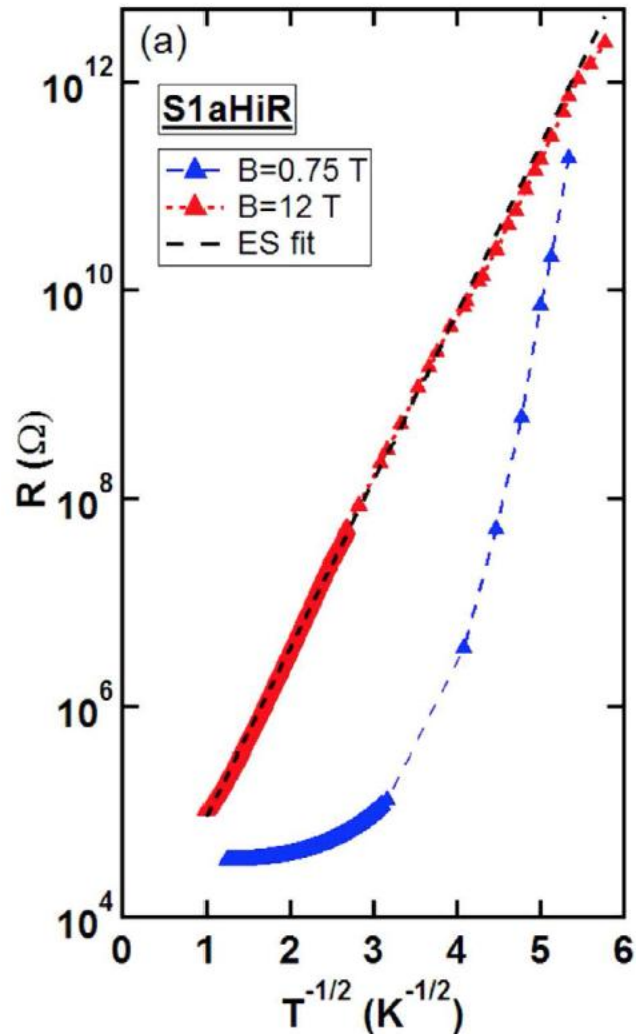
And if so, how

(given that we do not yet know how to measure the growth of entanglement)

can one distinguish many-body localized states from “classical” glassy states?

InO Film for $B > B_{\text{SIT}} \sim 0.5 \text{ T}$

M. Ovadia *et al*, Scientific Reports **5**, 13503 (2015)



InO Film for $B > B_{SIT} \sim 0.5$ T

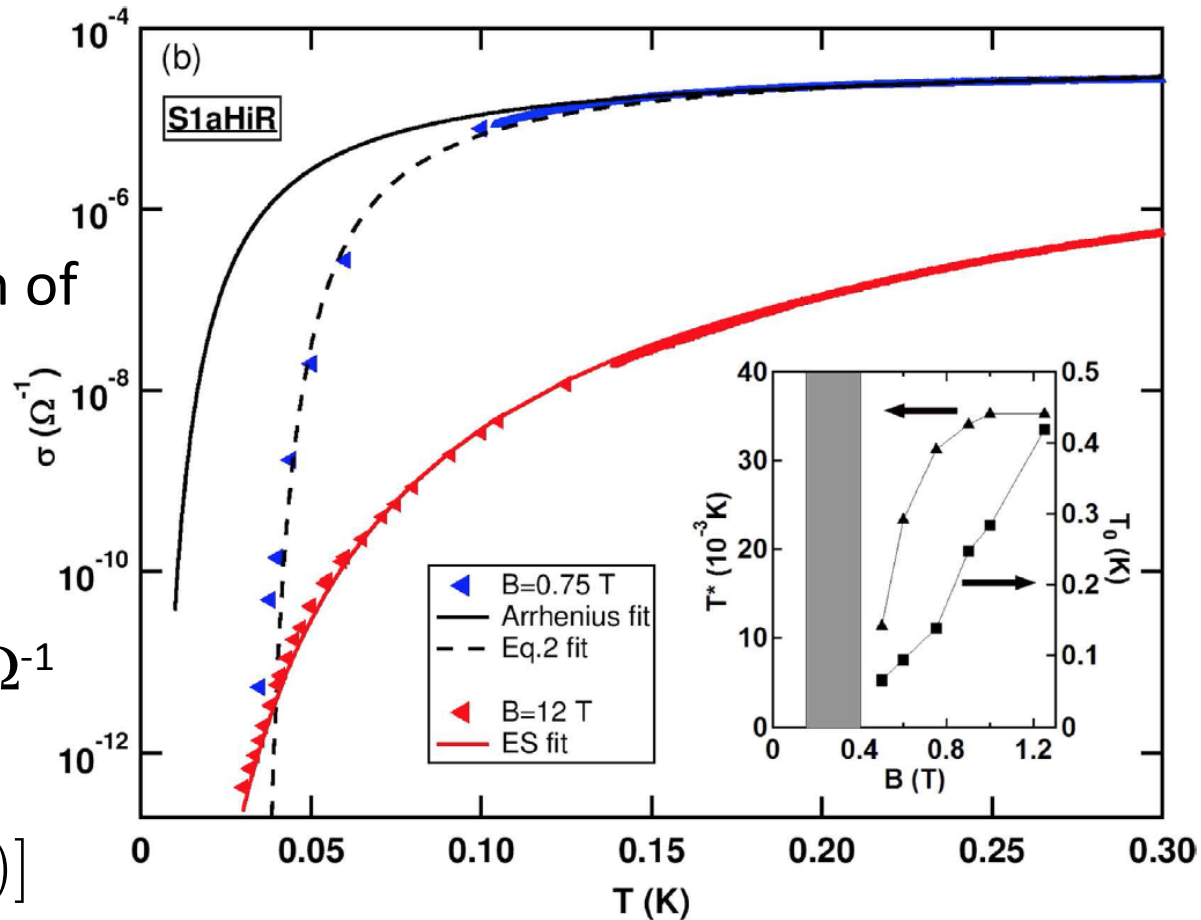
M. Ovadia *et al*, Scientific Reports **5**, 13503 (2015)

Superconducting quantum of conductance:

$$\sigma_Q = (2e)^2/h$$

$$= 1.59184494207 \cdot 10^{-4} \Omega^{-1}$$

$$\rho = \rho_0 \exp[T_0/(T - T^*)]$$



$$T_0 = 0.138K, \quad T^* = 0.031K, \quad T_{min} = 0.042K = [1.35]T^*$$

The Glass Transition in Supercooled Liquids

“In Search of a Theory of
Supercooled Liquids”

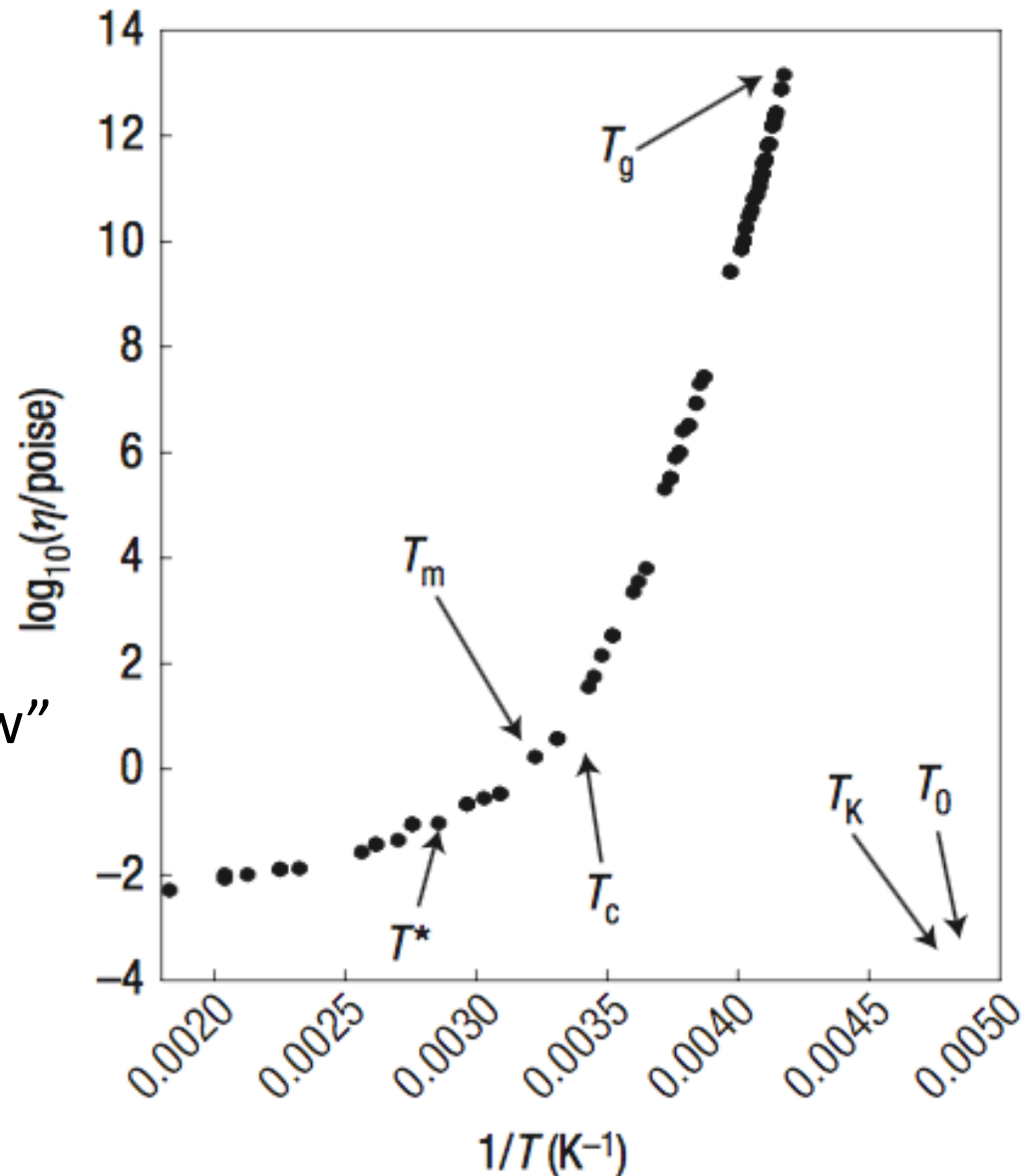
SAK and G. Tarjus

Nature Materials **7**, 831 (2008).

$$\eta(T) \sim \exp [DT_0/(T - T_0)]$$

“Volger-Fulcher-Tammann Law”

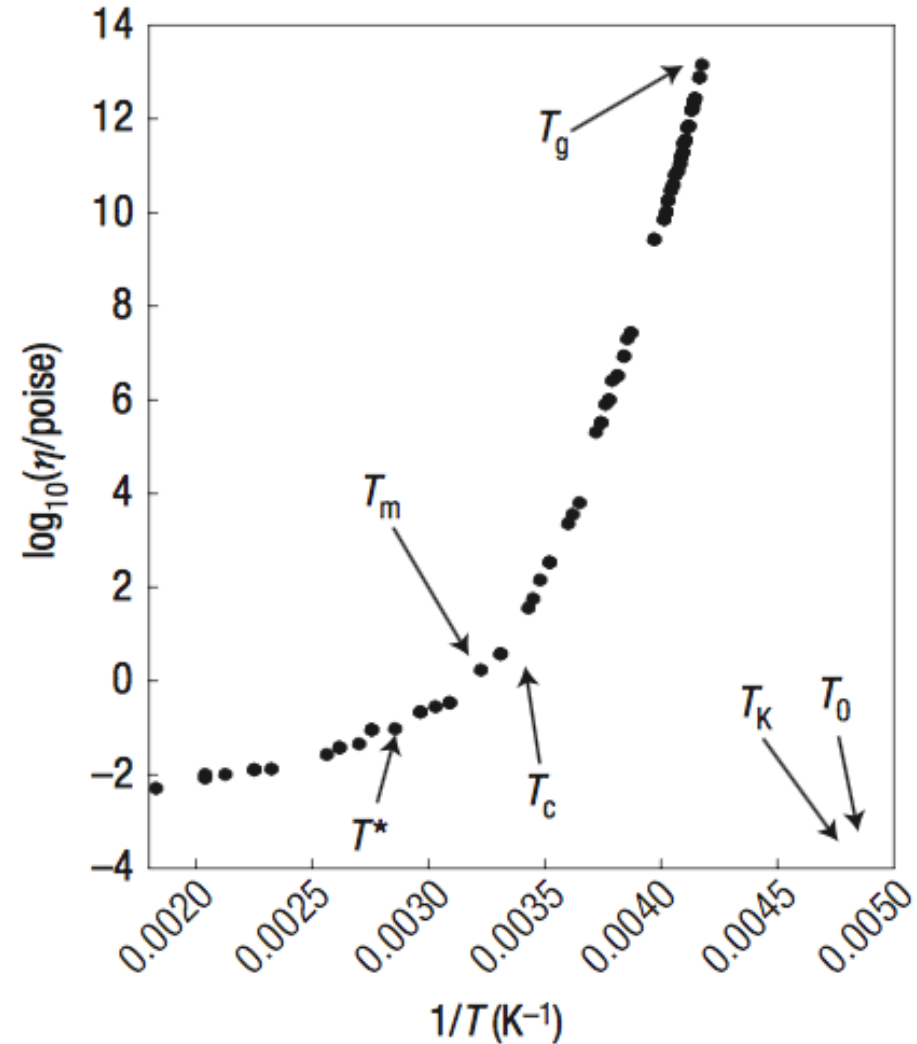
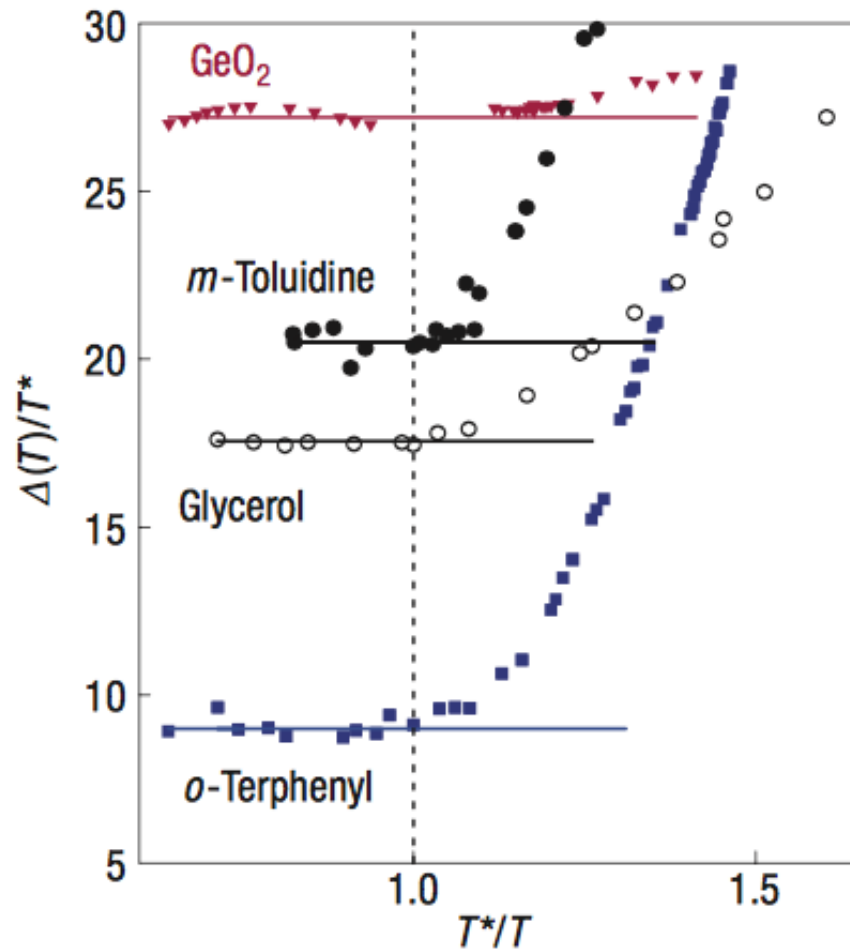
At T_g , typically $T > 1.2T_0$



$$\eta(T) = \eta_{\infty} \exp[\Delta(T)/T]$$

$$\Delta(T) \approx E_{\infty} + \Theta(T^* - T)E_1(1 - T/T^*)^x$$

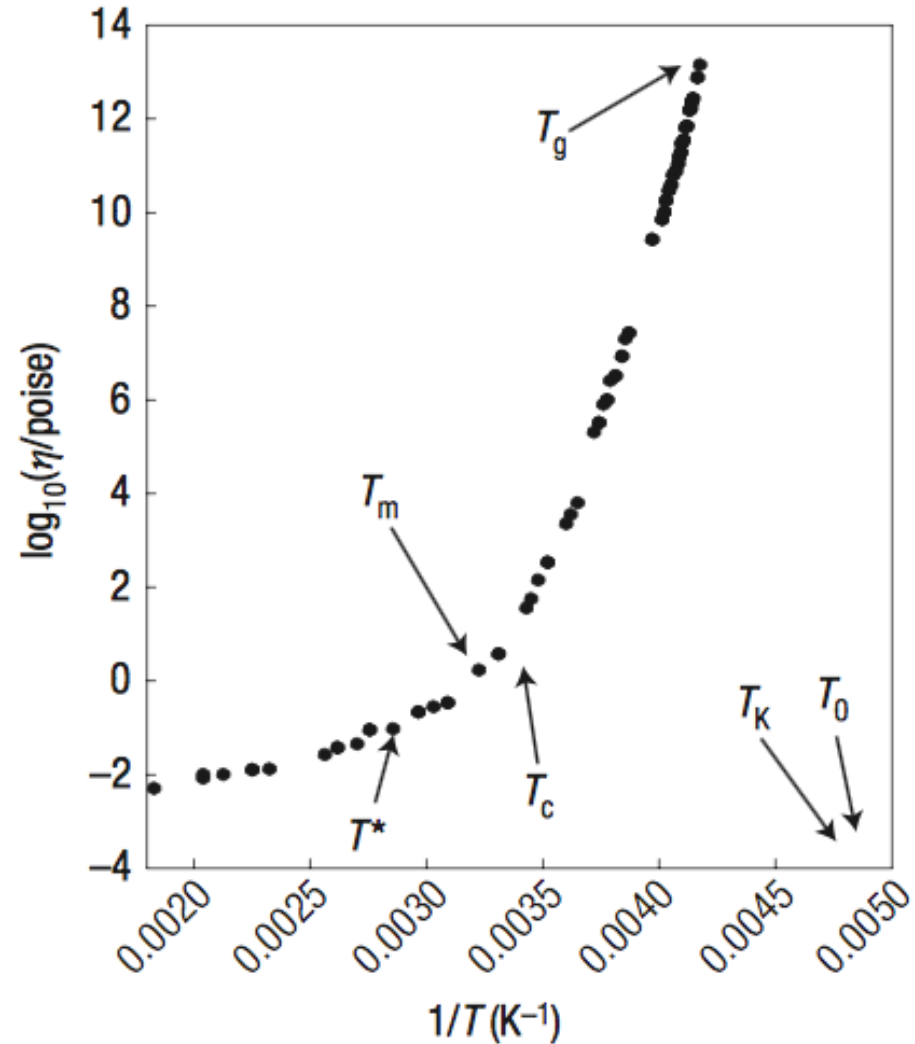
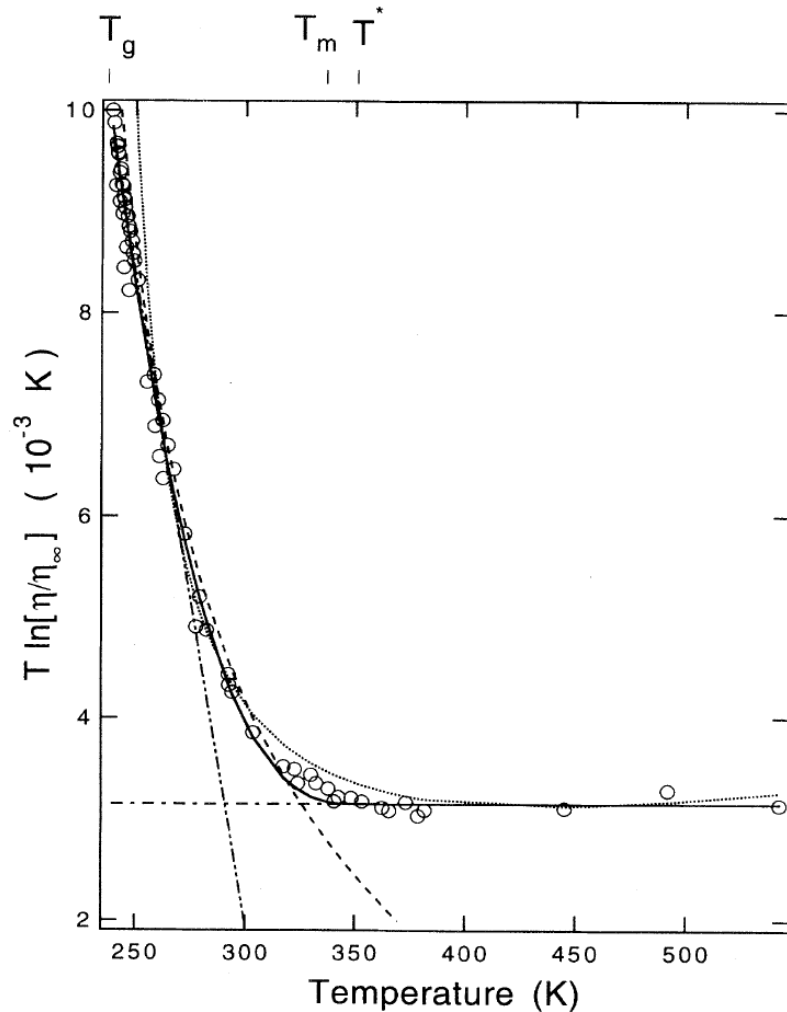
with $x \approx 8/3$



$$\eta(T) = \eta_{\infty} \exp[\Delta(T)/T]$$

$$\Delta(T) \approx E_{\infty} + \Theta(T^* - T)E_1(1 - T/T^*)^x$$

with $x \approx 8/3$

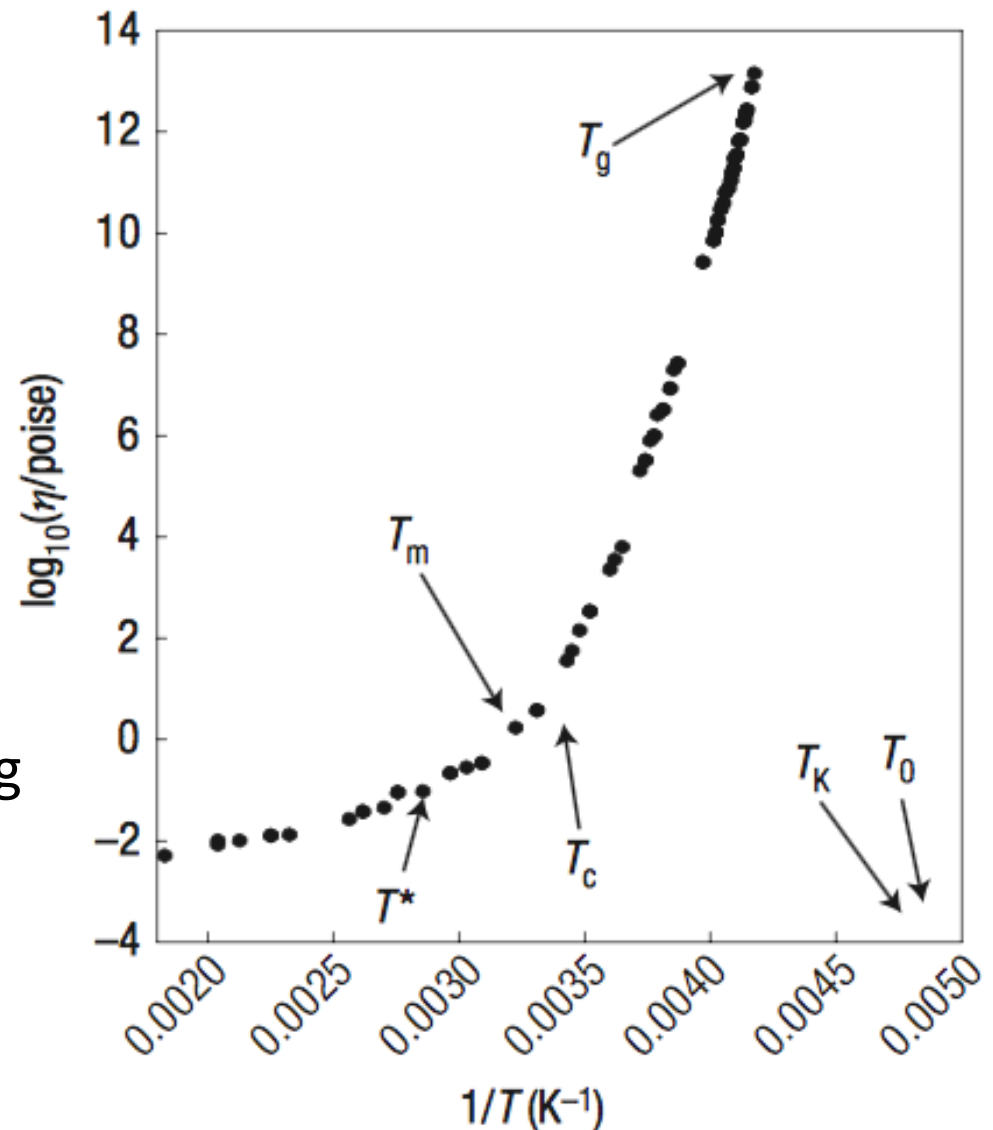


$$\eta(T) \sim \exp [DT_0/(T - T_0)]$$

This is a purely classical phenomenon

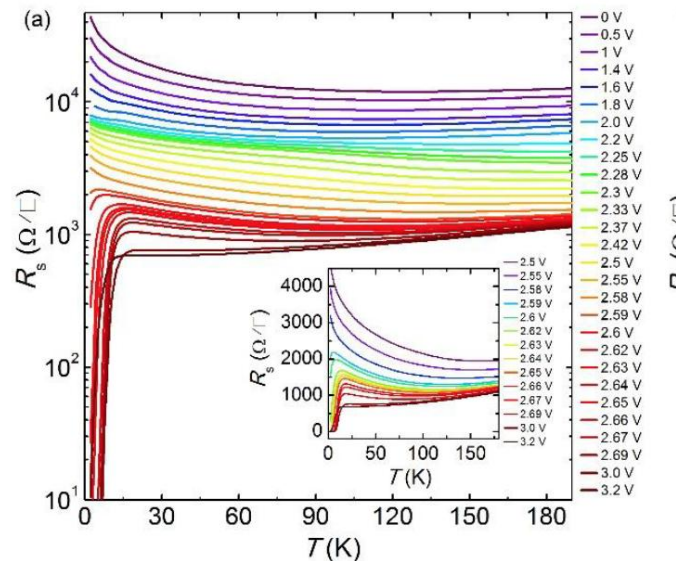
There may or may not be an “ideal glass” transition at $T=T_0$

No doubt something resembling a classical glass transition in an electronic system would be exceedingly interesting itself.

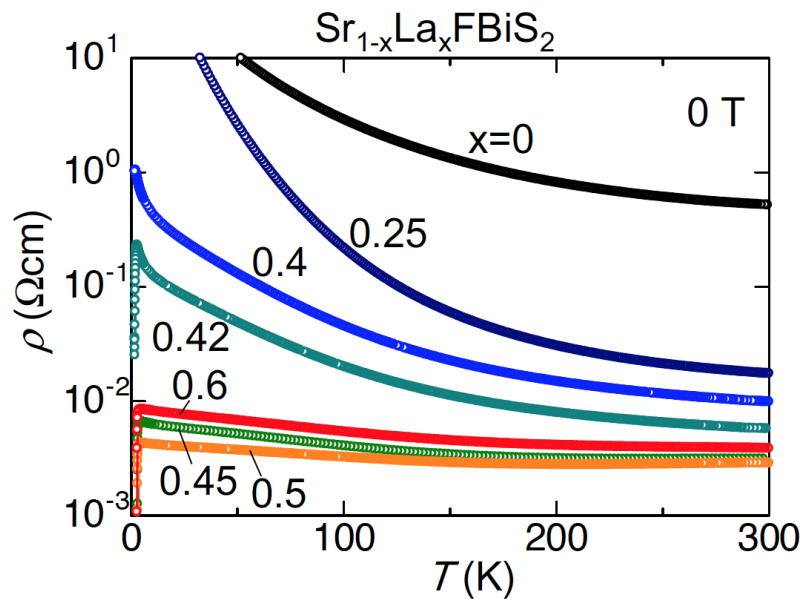


In any case, this raises the issue of how to distinguish an “apparent” classical glass transition from an “almost” MBL

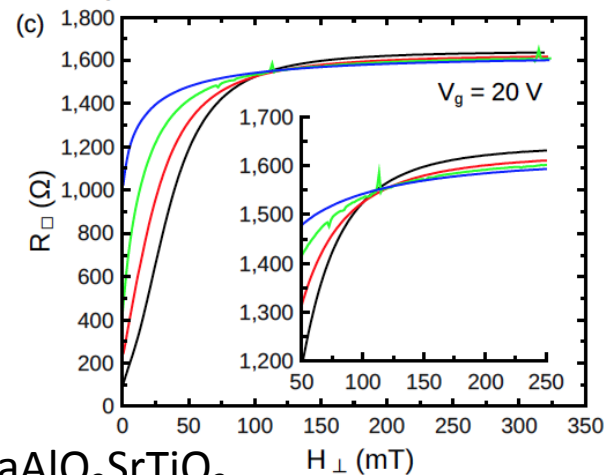
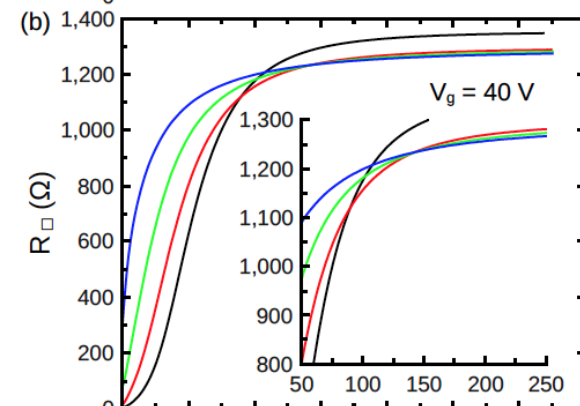
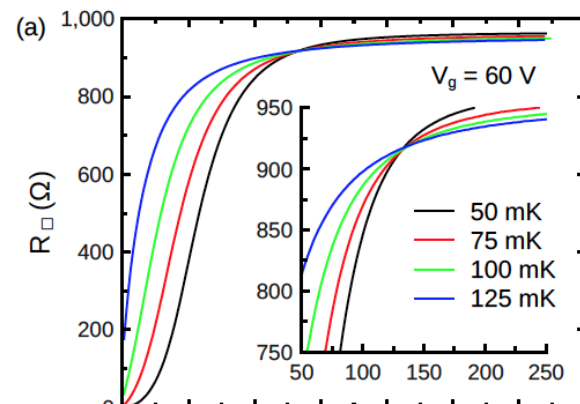
Thanks



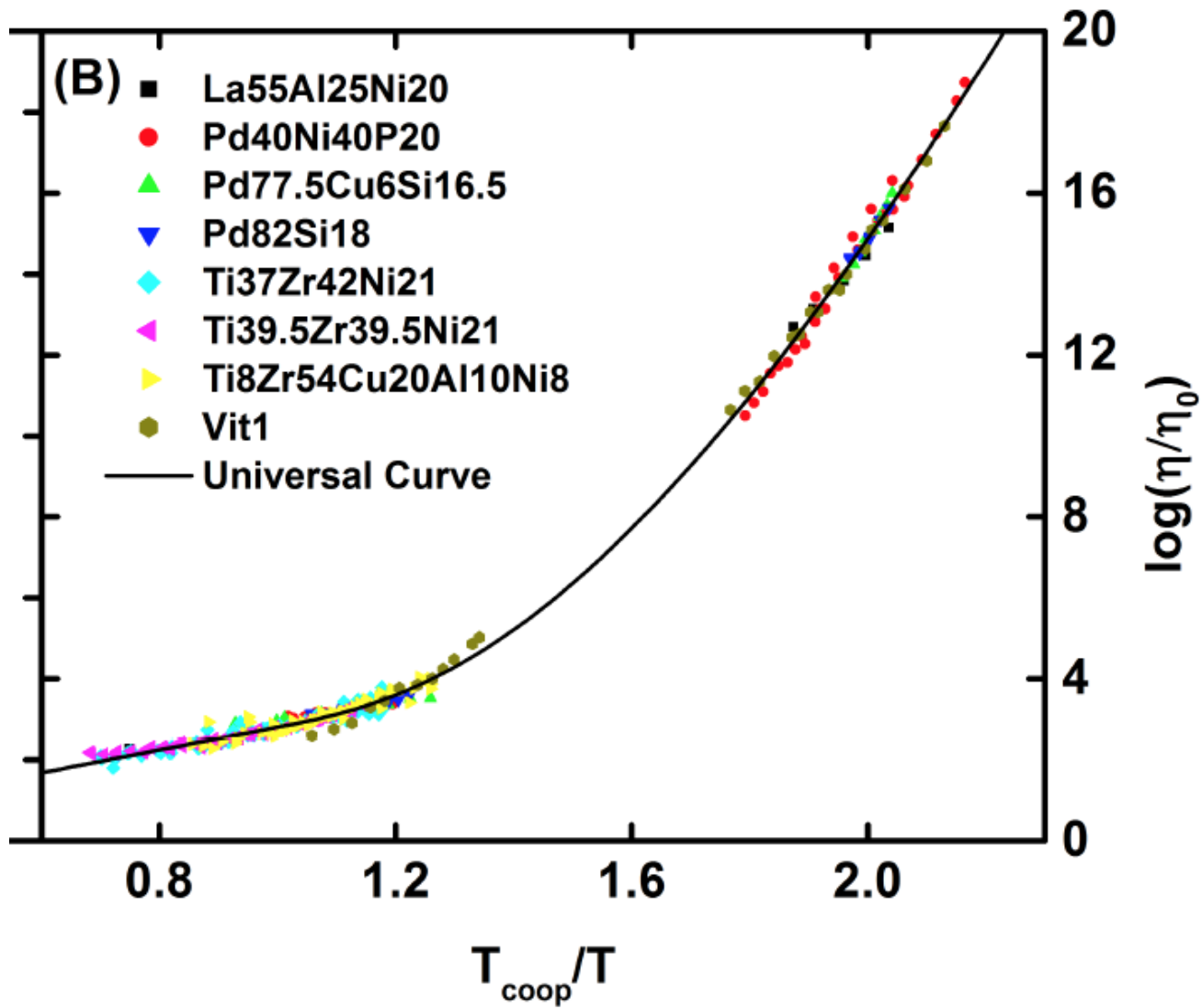
Gated electron-doped cuprate
arXiv:1507.01668



arXiv:1311.5117



LaAlO₃SrTiO₃
arXiv1309.3612



[M. Blodgett, T. Egami, Z. Nussinov, K. F. Kelton](#), ArXiv:1407.7558